

MUN5232DW1, NSBC143EDXV6, NSBC143EDP6

Dual NPN Bias Resistor Transistors R1 = 4.7 kΩ, R2 = 4.7 kΩ

NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

(T_A = 25°C, common for Q₁ and Q₂, unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current – Continuous	I _C	100	mA _{dc}
Input Forward Voltage	V _{IN(fwd)}	30	Vdc
Input Reverse Voltage	V _{IN(rev)}	10	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

Device	Package	Shipping†
MUN5232DW1T1G, SMUN5232DW1T1G	SOT-363	3,000/Tape & Reel
NSBC143EDXV6T1G	SOT-563	4,000/Tape & Reel
NSBC143EDP6T5G	SOT-963	8,000/Tape & Reel

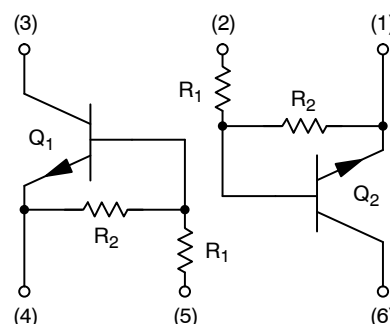
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



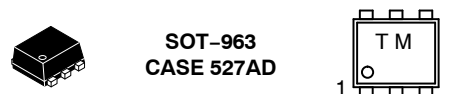
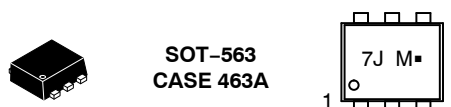
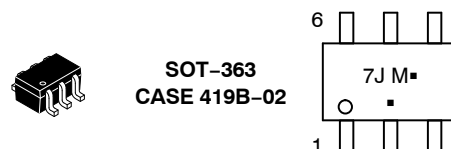
ON Semiconductor®

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PIN CONNECTIONS



MARKING DIAGRAMS



7J/T = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
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MUN5232DW1 (SOT-363) ONE JUNCTION HEATED

Total Device Dissipation T _A = 25°C (Note 37) (Note 38) Derate above 25°C (Note 37) (Note 38)	P _D	187 256 1.5 2.0	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 37) (Note 38)	R _{θJA}	670 490	°C/W

MUN5232DW1 (SOT-363) BOTH JUNCTION HEATED (Note 39)

Total Device Dissipation T _A = 25°C (Note 37) (Note 38) Derate above 25°C (Note 37) (Note 38)	P _D	250 385 2.0 3.0	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 37) (Note 38)	R _{θJA}	493 325	°C/W
Thermal Resistance, Junction to Lead (Note 37) (Note 38)	R _{θJL}	188 208	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

NSBC143EDXV6 (SOT-563) ONE JUNCTION HEATED

Total Device Dissipation T _A = 25°C (Note 37) Derate above 25°C (Note 37)	P _D	357 2.9	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 37)	R _{θJA}	350	°C/W

NSBC143EDXV6 (SOT-563) BOTH JUNCTION HEATED (Note 39)

Total Device Dissipation T _A = 25°C (Note 37) Derate above 25°C (Note 37)	P _D	500 4.0	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 37)	R _{θJA}	250	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

NSBC143EDP6 (SOT-963) ONE JUNCTION HEATED

Total Device Dissipation T _A = 25°C (Note 40) (Note 41) Derate above 25°C (Note 40) (Note 41)	P _D	231 269 1.9 2.2	MW mW/°C
Thermal Resistance, Junction to Ambient (Note 40) (Note 41)	R _{θJA}	540 464	°C/W

NSBC143EDP6 (SOT-963) BOTH JUNCTION HEATED (Note 39)

Total Device Dissipation T _A = 25°C (Note 40) (Note 41) Derate above 25°C (Note 40) (Note 41)	P _D	339 408 2.7 3.3	MW mW/°C
Thermal Resistance, Junction to Ambient (Note 40) (Note 41)	R _{θJA}	369 306	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

37. FR-4 @ Minimum Pad.

38. FR-4 @ 1.0 × 1.0 Inch Pad.

39. Both junction heated values assume total power is sum of two equally powered channels.

40. FR-4 @ 100 mm², 1 oz. copper traces, still air.

41. FR-4 @ 500 mm², 1 oz. copper traces, still air.

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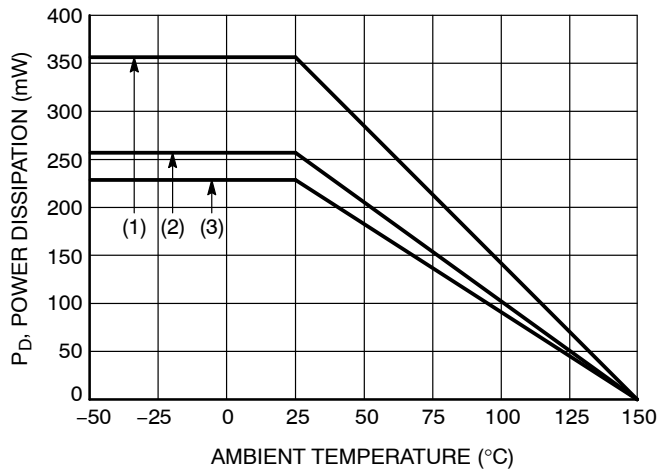
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, common for Q_1 and Q_2 , unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}$, $I_E = 0$)	I_{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}$, $I_B = 0$)	I_{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}$, $I_C = 0$)	I_{EBO}	–	–	1.5	mAdc
Collector-Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 42) ($I_C = 2.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	50	–	–	Vdc

ON CHARACTERISTICS

DC Current Gain (Note 42) ($I_C = 5.0\text{ mA}$, $V_{CE} = 10\text{ V}$)	h_{FE}	15	30	–	
Collector-Emitter Saturation Voltage (Note 42) ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$)	$V_{CE(sat)}$	–	–	0.25	V
Input Voltage (Off) ($V_{CE} = 5.0\text{ V}$, $I_C = 100\text{ }\mu\text{A}$)	$V_{i(off)}$	–	1.2	–	Vdc
Input Voltage (On) ($V_{CE} = 0.2\text{ V}$, $I_C = 20\text{ mA}$)	$V_{i(on)}$	–	2.4	–	Vdc
Output Voltage (On) ($V_{CC} = 5.0\text{ V}$, $V_B = 2.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	V_{OL}	–	–	0.2	Vdc
Output Voltage (Off) ($V_{CC} = 5.0\text{ V}$, $V_B = 0.25\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	–	–	Vdc
Input Resistor	R_1	3.3	4.7	6.1	$\text{k}\Omega$
Resistor Ratio	R_1/R_2	0.8	1.0	1.2	

42. Pulsed Condition: Pulse Width = 300 ms, Duty Cycle $\leq 2\%$.



- (1) SOT-363; 1.0 x 1.0 Inch Pad
- (2) SOT-563; Minimum Pad
- (3) SOT-963; 100 mm², 1 oz. Copper Trace

Figure 98. Derating Curve

TYPICAL CHARACTERISTICS
MUN5232DW1, NSBC143EDXV6

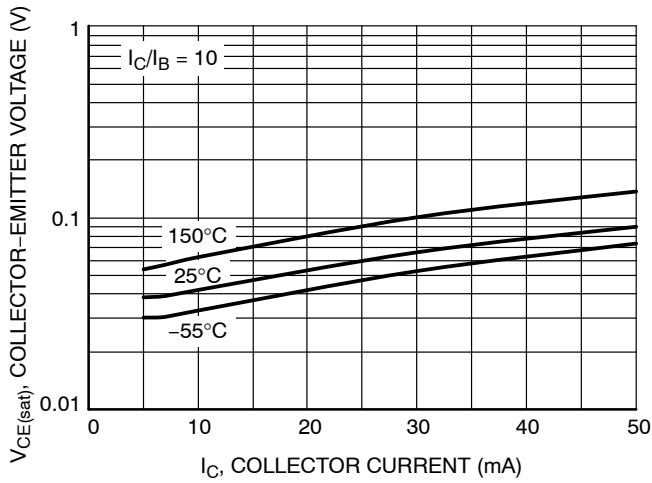


Figure 99. $V_{CE(sat)}$, vs. I_C

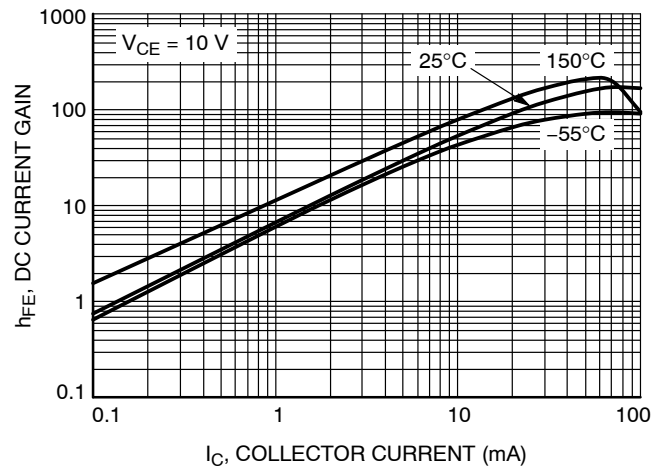


Figure 100. DC Current Gain

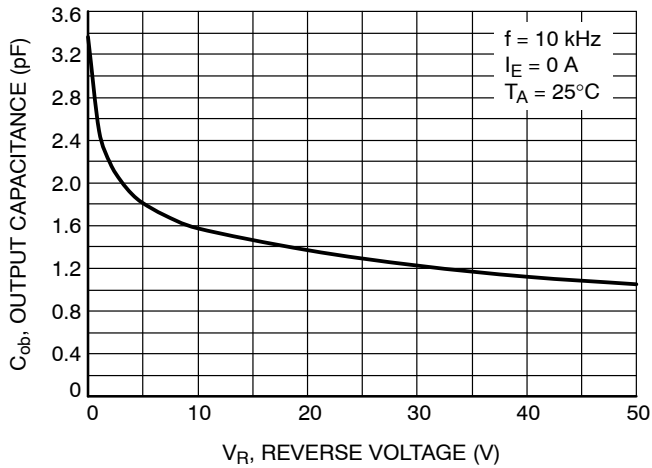


Figure 101. Output Capacitance

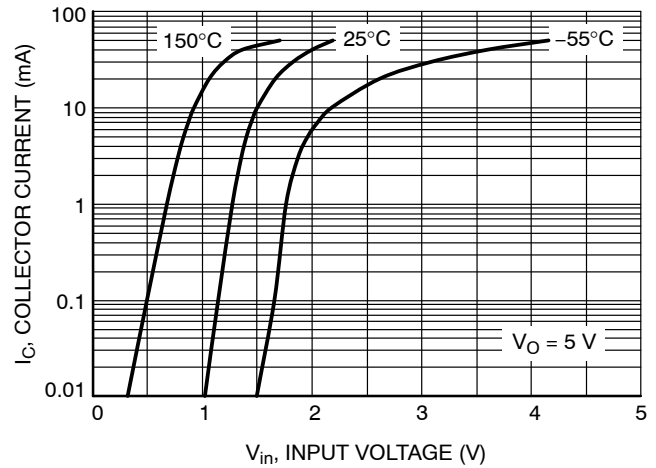


Figure 102. Output Current vs. Input Voltage

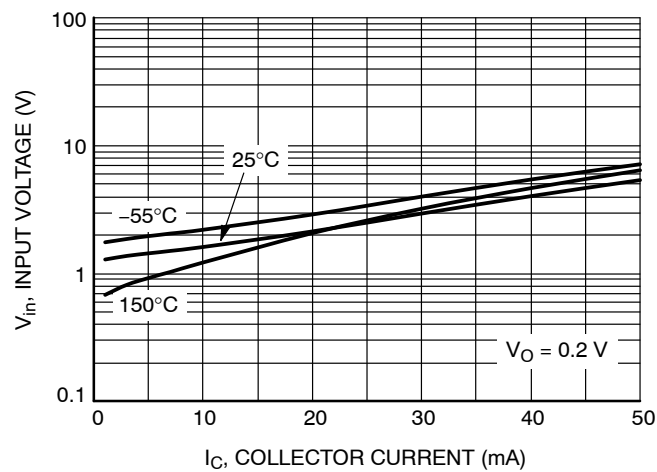


Figure 103. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS
NSBC143EDP6

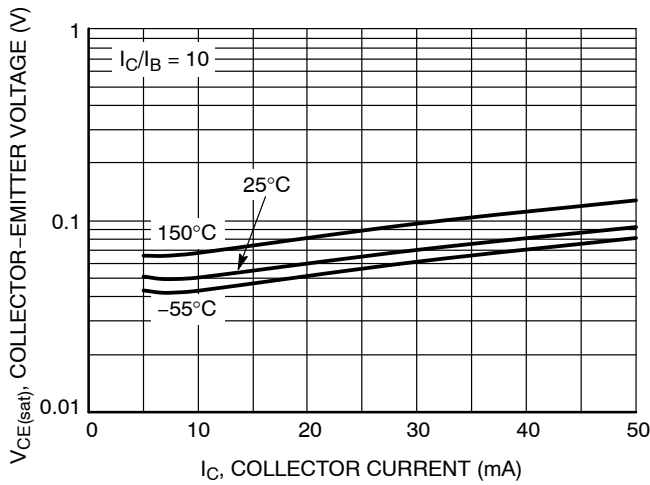


Figure 104. $V_{CE(sat)}$, vs. I_C

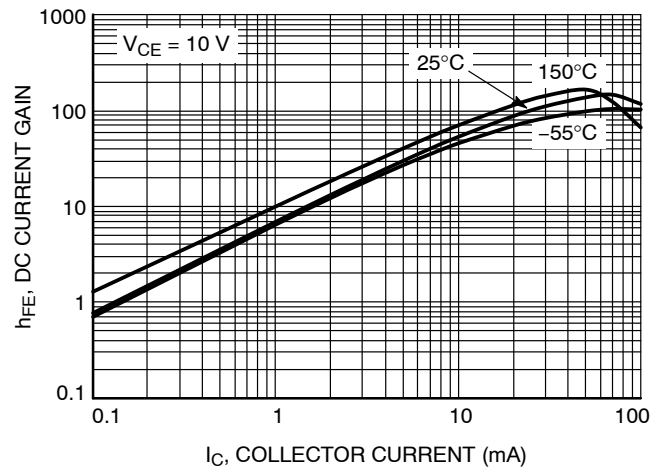


Figure 105. DC Current Gain

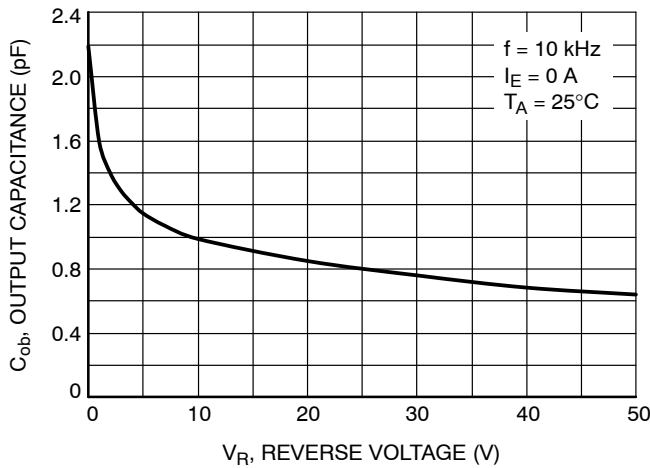


Figure 106. Output Capacitance

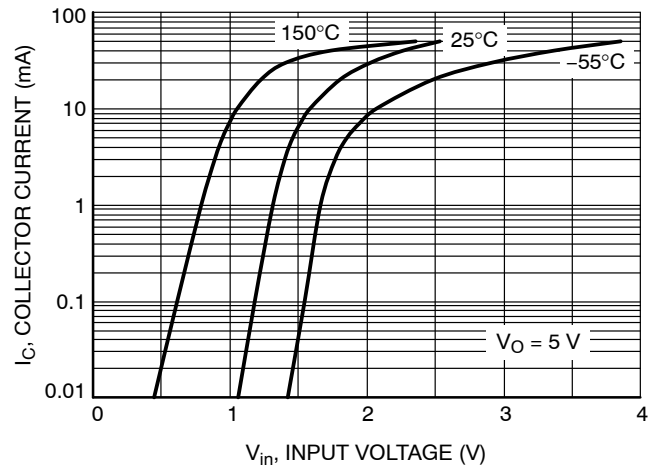


Figure 107. Output Current vs. Input Voltage

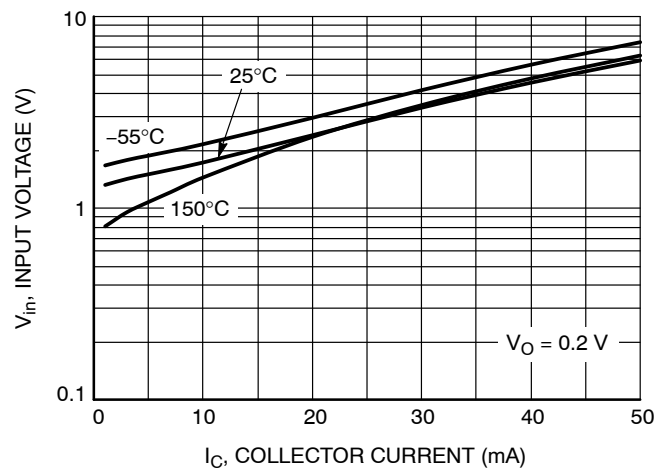
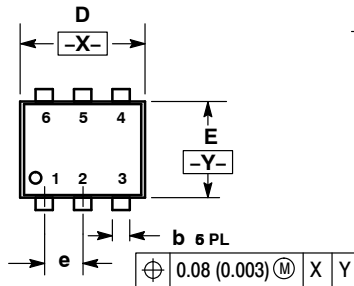


Figure 108. Input Voltage vs. Output Current

PACKAGE DIMENSIONS

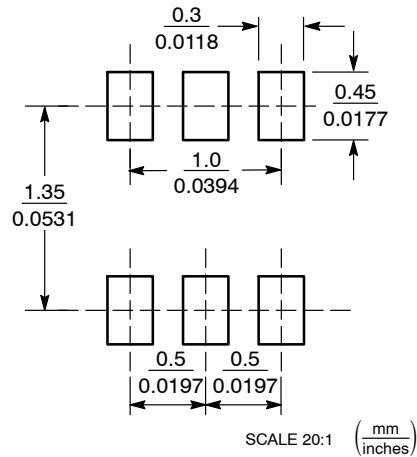
SOT-563, 6 LEAD
CASE 463A
ISSUE G

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H _E	1.50	1.60	1.70	0.059	0.062	0.066

SOLDERING FOOTPRINT*

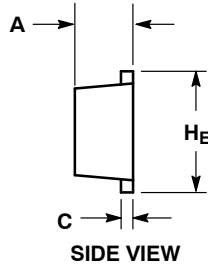
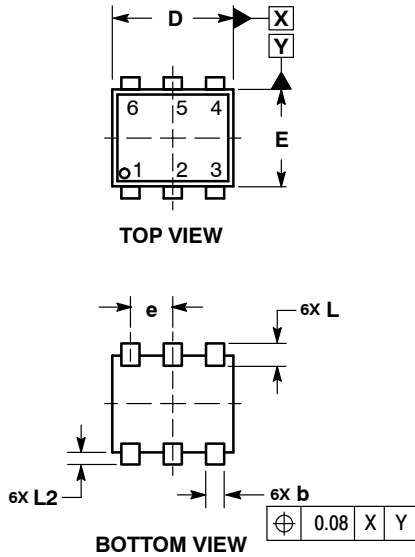


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MUN5232DW1, NSBC143EDXV6, NSBC143EDP6

PACKAGE DIMENSIONS

SOT-963 CASE 527AD ISSUE E

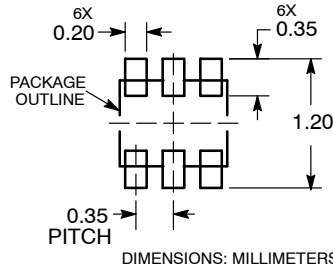


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.10	0.15	0.20
C	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H _E	0.95	1.00	1.05
L	0.19 REF		
L2	0.05	0.10	0.15

RECOMMENDED MOUNTING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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